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Please enter the revised abstract
MK
10/18/04

# FACSIMILE TRANSMITTAL SHEET



TO: Examiner Nathan Ha
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FROM: James C. Kesterson
Slater & Matsil, L.L.P.

DATE: October 19, 2004
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RE:
**Applicant:** **Lee, *et al.***
**Serial No.:** **09/988,183**
**Date Filed:** **November 19, 2001**
**Docket No.:** **2001 P 11904 US**
**Art Unit:** **2814**
**Title:** **Formation of Dual Work Function Gate Electrode**

**SUPPLEMENTAL AMENDMENT AFTER FINAL REJECTION**

Per your conversation with Jim Kesterson today, below please find a revised abstract for the above referenced case:

A method of manufacturing a dual work function gate electrode used with a CMOS structure. Penetration of the boron doping material into the channel region is suppressed without causing boron depletion near the gate oxide region by laser annealing a layer of a- Si covering poly- Si and the gate oxide at its nMOS site and the pMOS site. The laser annealing is accomplished at an energy level sufficient to melt a portion of the a- Si, but insufficient to melt the poly- Si. Avoiding melting of the poly- Si reduces gate oxide damage.

The abstract has been rewritten in compliance with proper U.S. Patent Office Procedure.

James C. Kesterson

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